

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SD2124(L)/(S)

Silicon NPN Epitaxial

RENESAS

ADE-208-927 (Z)

1st. Edition

September 2000

Application

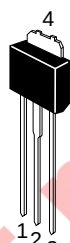
Low frequency power amplifier

Outline

DPAK

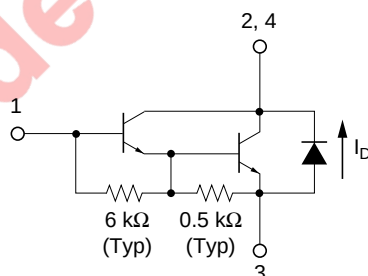


S Type



L Type

- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector



Absolute Maximum Ratings (Ta = 25°C)

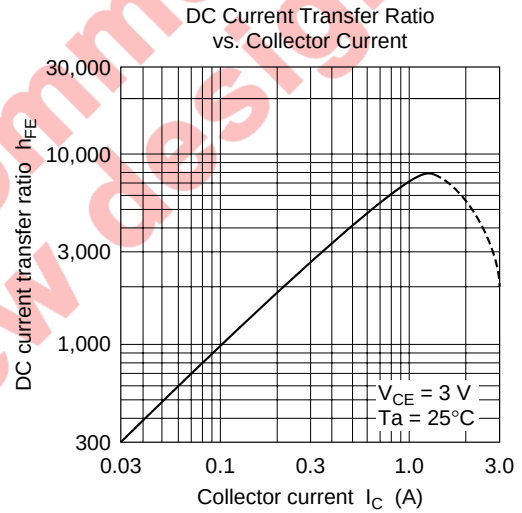
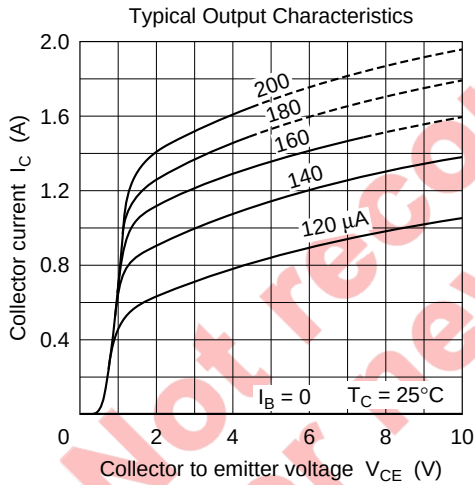
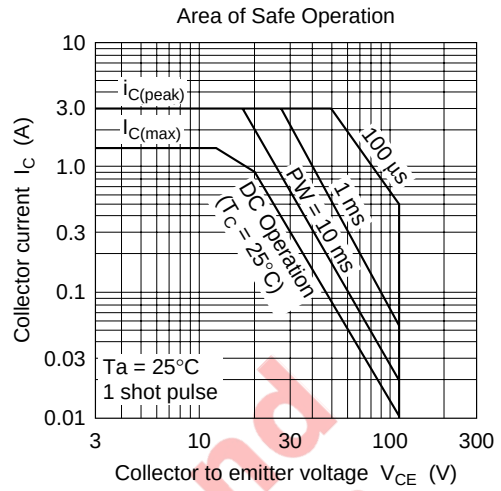
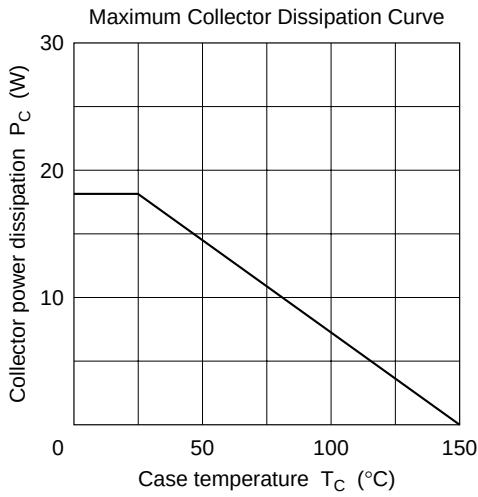
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	120	V
Collector to emitter voltage	V_{CEO}	120	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I_C	1.5	A
Collector peak current	$I_{C(peak)}$	3.0	A
Collector power dissipation	P_C^{*1}	18	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C
C to E diode forward current	I_D^{*1}	1.5	A

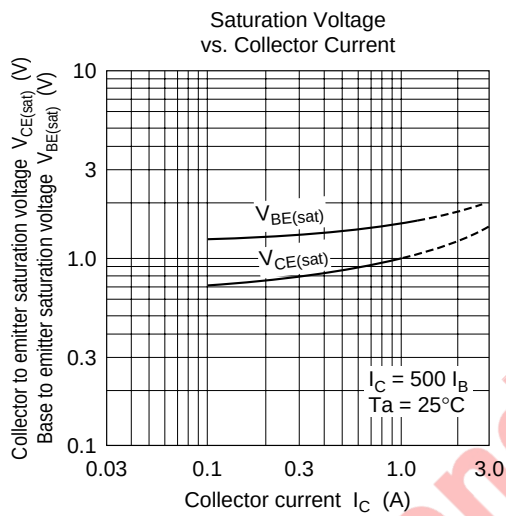
Note: 1. Value at T_C = 25°C.

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	120	—	—	V	$I_C = 0.1 \text{ mA}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	120	—	—	V	$I_C = 10 \text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 50 \text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{CB} = 100 \text{ V}$, $I_E = 0$
	I_{CEO}	—	—	10		$V_{CE} = 100 \text{ V}$, $R_{BE} = \infty$
DC current transfer ratio	h_{FE}	2000	—	30000		$V_{CE} = 3 \text{ V}$, $I_C = 1 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.5	V	$I_C = 1 \text{ A}$, $I_B = 1 \text{ mA}^{*1}$
	$V_{CE(sat)}$	—	—	2.0		$I_C = 1.5 \text{ A}$, $I_B = 1.5 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	2.0	V	$I_C = 1 \text{ A}$, $I_B = 1 \text{ mA}^{*1}$
	$V_{BE(sat)}$	—	—	2.5		$I_C = 1.5 \text{ A}$, $I_B = 1.5 \text{ mA}^{*1}$
C to E diode forward voltage	V_D	—	—	3.0	V	$I_D = 1.5 \text{ A}^{*1}$
Turn on time	t_{on}	—	0.5	—	μs	$I_C = 1 \text{ A}$, $I_{B1} = -I_{B2} = 1 \text{ mA}$
Turn off time	t_{off}	—	2.0	—	μs	

Note: 1. Pulse test.





Not recommended
for new design

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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U S A
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Domacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 0104
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071